Supporting Information

Boosting Performances of Triboelectric Nanogenerators by Optimizing Dielectric Properties and Thickness of Electrification Layer

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Fig. S1. (a) XRD patterns and (b) FTIR spectra of BaTiO₃/PVDF nanocomposite films with different filler contents.



Fig. S2. Cross-sectional SEM images for PVDF-based films with various BaTiO₃ volume fraction (4.96 vol%. 6.89 vol%. 8.98 vol%. 13.74 vol%).



Fig. S3. Cross-sectional SEM images for PVDF-based films with various BaTiO₃ volume fraction (4.96 vol%. 6.89 vol%. 8.98 vol%. 13.74 vol%).



Fig. S4. (a) (b) The elemental mapping showing the dispersion states of nanoparticles in the representative $BaTiO_3/PVDF$ composite film with 11.25 vol%.



Fig. S5. (a) Frequency dependence of dielectric loss values for PVDF-based films with various $BaTiO_3$ volume fraction ranging from 0 to 16.47 vol%. The variation of (b) dielectric loss at 1000 Hz for PVDF-based films with various $BaTiO_3$ volume fraction.



Fig. S6. A photograph of as-fabricated TENGs.



Fig. S7. Potential distribution of TENG. (a) the gap distance is 5 μ m. (a) the gap distance is 1 mm.



Fig. S8. Cross-sectional SEM image of Nylon.